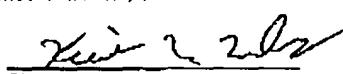


IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
Suzuki, et al. §
§ Group Art Unit: 2818
Serial No.: 10/004,489 §
§ Examiner: Renee R. Berry
Confirmation No.: 9428 §
§
Filed: October 23, 2001 §
§
For: Method of Forming Film, Method
of Manufacturing Semiconductor
Device and Film Forming
Apparatus §
§

Mail Stop Issue Fee
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

CERTIFICATE OF FACSIMILE TRANSMISSION UNDER 37 CFR 1.8	
I hereby certify that this correspondence and the documents referred to as attached therein are being facsimile transmitted to the U.S. Patent and Trademark Office to the fax number indicated by the Examiner, namely, fax number (703)-872-9306 to the attention of the named Examiner, on the date below.	
1/13/04 Date	 Signature

COMMENTS ON STATEMENT OF REASONS FOR ALLOWANCE

In the Notice of Allowance mailed December 5, 2003, the Examiner states that there is no prior art of record that teaches or suggests a method of depositing a halogen-doped silicon oxide over metal lines by using gas mixtures having SiF₄:SiH₄ ratios of 0.0 to 1.0. Applicants note that the claim 1 of the allowed claims recites a flow rate ratio of SiF₄ to SiH₄ of larger than 1, rather than a SiF₄:SiH₄ ratio of 0.0 to 1.0. Applicants submit that the references of record do not teach, show, or suggest a deposition method of forming a silicon inorganic insulating film on a substrate, comprising placing a substrate in a semiconductor manufacturing apparatus having parallel plate type electrodes, and depositing a fluorine-containing silicon insulating film on the substrate by generating a plasma of a process gas containing SiH₄, SiF₄, and an oxygen source substance, wherein a flow rate ratio of said SiF₄ to said SiH₄ into the

Jan-13-04 05:51pm From-Moser, Patterson & Sheridan L.L.P.

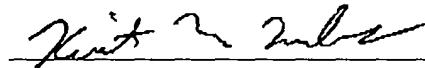
+713 623 4846

T-538 P 008/008 F-619

PATENT
Atty. Dkt. No. AMAT/3819/DSM/BCVD/JW

semiconductor manufacturing apparatus is larger than 1, as recited in claim 1.

Respectfully submitted,



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